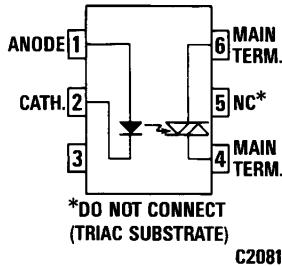
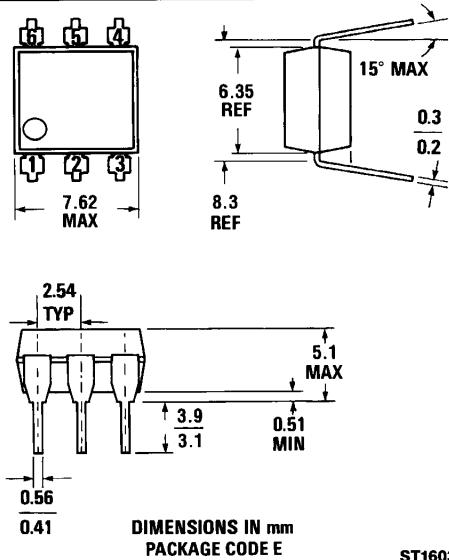


## NON-ZERO-CROSSING TRIACS

**MOC3020 MOC3021  
MOC3022 MOC3023**

### PACKAGE DIMENSIONS



ST1603

Equivalent Circuit

### ABSOLUTE MAXIMUM RATINGS

#### TOTAL PACKAGE

Storage temperature .....	-55°C to 150°C
Operating temperature .....	-40°C to 100°C
Lead temperature (soldering, 10 sec) .....	260°C

#### INPUT DIODE

Forward DC current .....	50 mA
Reverse voltage .....	3 V
Peak forward current (1 μs pulse, 300 pps) .....	3.0 A
Power dissipation (25°C ambient) .....	100 mW
Derate linearly (above 25°C ambient) .....	1.33 mW/°C

#### OUTPUT DRIVER

Off-state output terminal voltage .....	400 Volts
On-state RMS current $T_A=25^\circ\text{C}$ .....	100 mA
(Full cycle, 50 to 60 Hz) $T_A=70^\circ\text{C}$ .....	50 mA
Peak nonrepetitive surge current .....	1.2 A
(PW=10 ms, DC=10%) .....	
Total power dissipation (25°C ambient) .....	300 mW
Derate above 25°C .....	4.0 mW/°C



## NON-ZERO-CROSSING TRIACS

### ELECTRO-OPTICAL CHARACTERISTICS (25°C Temperature Unless Otherwise Specified)

INDIVIDUAL COMPONENT CHARACTERISTICS						
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
<b>INPUT DIODE</b>						
Forward voltage	V <sub>F</sub>		1.2	1.50	V	I <sub>F</sub> =10 mA
Junction capacitance	C <sub>J</sub>		50		pF	V <sub>F</sub> =0 V, f=1 MHz
Reverse leakage current	I <sub>R</sub>			100	μA	V <sub>R</sub> =3.0 V
<b>OUTPUT DETECTOR</b>						
Peak blocking current, either direction	I <sub>DRM</sub>	—	10	100	nA	V <sub>DRM</sub> =400 V, Note 1
Peak on-state voltage, either direction	V <sub>TM</sub>	—	2.5	3.0	Volts	I <sub>TM</sub> =100 mA Peak

Note 1. Test voltage must be applied within dv/dt rating.

### TRANSFER CHARACTERISTICS

DC CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
LED trigger current (current required to latch output)	MOC3020 I <sub>FT</sub>	—	—	30	mA	Main terminal voltage=3.0 V, R <sub>L</sub> =150Ω
	MOC3021 I <sub>FT</sub>	—	—	15	mA	
	MOC3022 I <sub>FT</sub>	—	—	10	mA	
	MOC3023 I <sub>FT</sub>	—	—	5	mA	
Holding current	I <sub>H</sub>	—	100	—	μA	Either direction

### TRANSFER CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
<b>dv/dt RATING</b>						
Critical rate of rise of off-state voltage	dv/dt	—	12	—	V/μs	Static dv/dt, T <sub>A</sub> =85°C (see Fig. 3)
Critical rate of rise of commutating voltage	dv/dt	—	0.2	—	V/μs	Commutating dv/dt I <sub>LOAD</sub> =15 mA (see Fig. 4)

### ISOLATION CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Isolation voltage	V <sub>ISO</sub>	5300			V <sub>AC</sub> RMS	I <sub>IO</sub> <1 μA, 1 Minute
	V <sub>ISO</sub>	7500			V <sub>AC</sub> PEAK	I <sub>IO</sub> <1 μA, 1 Minute
Isolation resistance	R <sub>ISO</sub>	10 <sup>11</sup>			ohms	V <sub>IO</sub> =500 VDC
Isolation capacitance	C <sub>ISO</sub>		0.5		pF	f=1 MHz

Note 1: Ratings apply to either polarity of pin 6 — referenced to pin 4. Voltages must be applied within dv/dt rating.

**TYPICAL ELECTRICAL CHARACTERISTIC CURVES**

(25°C Free Air Temperature Unless Otherwise Specified)

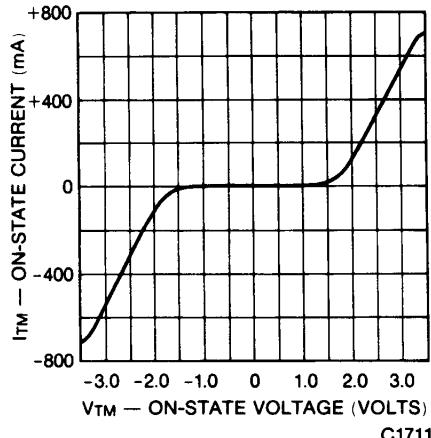


Fig. 1. On-State Characteristics

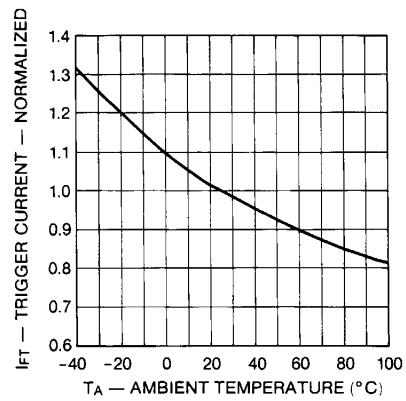
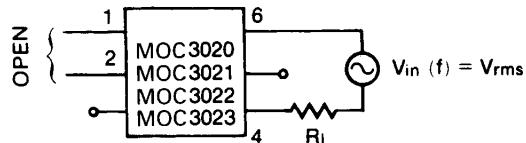


Fig. 2. Trigger Current vs. Temperature

**TEST CIRCUITS FOR dV/dt MEASUREMENTS**



$$\frac{dV}{dt} = \omega V_{\text{pack}} = 2\pi f \times 1.414 V_{\text{rms}} \\ = 8.88 f V_{\text{rms}}$$

Fig. 3. Static dV/dt

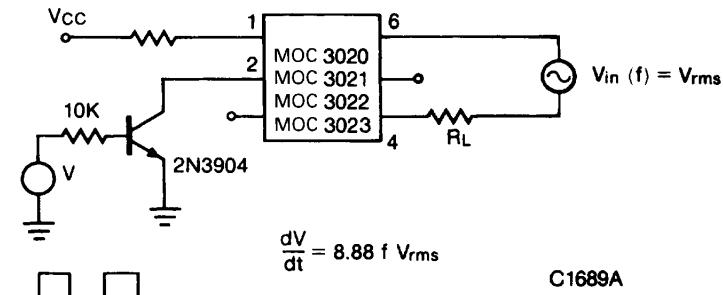


Fig. 4. Commutating dV/dt